

74HC1G125; 74HCT1G125

Bus buffer/line driver; 3-state

Rev. 05 — 23 December 2005

Product data sheet

1. General description

The 74HC1G125; 74HCT1G125 is a high-speed, Si-gate CMOS device.

The 74HC1G125; 74HCT1G125 provides one non-inverting buffer/line driver with 3-state output. The 3-state output is controlled by the output enable input (pin $\overline{\text{OE}}$). A HIGH level at pin $\overline{\text{OE}}$ causes the output to assume a high-impedance OFF-state.

The bus driver output currents are equal compared to the 74HC125 and 74HCT125.

2. Features

- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power consumption
- Balanced propagation delays
- ESD protection:
 - ◆ HBM EIA/JESD22-A114-C exceeds 2000 V
 - ◆ MM EIA/JESD22-A115-A exceeds 200 V
- Very small 5 pins packages
- Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$

3. Quick reference data

Table 1: Quick reference data

$GND = 0\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; $t_r = t_f \leq 6.0\text{ ns}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74HC1G125						
t_{PHL} , t_{PLH}	propagation delay A to Y	$V_{CC} = 5\text{ V}$; $C_L = 15\text{ pF}$	-	9	-	ns
C_i	input capacitance		-	1.5	-	pF
C_{PD}	power dissipation capacitance	$V_I = GND$ to V_{CC}	^[1] -	30	-	pF

PHILIPS

Table 1: Quick reference data ...continued

GND = 0 V; $T_{amb} = 25^{\circ}\text{C}$; $t_r = t_f \leq 6.0\text{ ns}$.

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74HCT1G125						
t_{PHL} , t_{PLH}	propagation delay A to Y	$V_{CC} = 5\text{ V}$; $C_L = 15\text{ pF}$	-	10	-	ns
C_i	input capacitance		-	1.5	-	pF
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC} - 1.5\text{ V}$	[1]	27	-	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW). $P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where: f_i = input frequency in MHz; f_o = output frequency in MHz; C_L = output load capacitance in pF; V_{CC} = supply voltage in V; N = number of inputs switching; $\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

4. Ordering information

Table 2: Ordering information

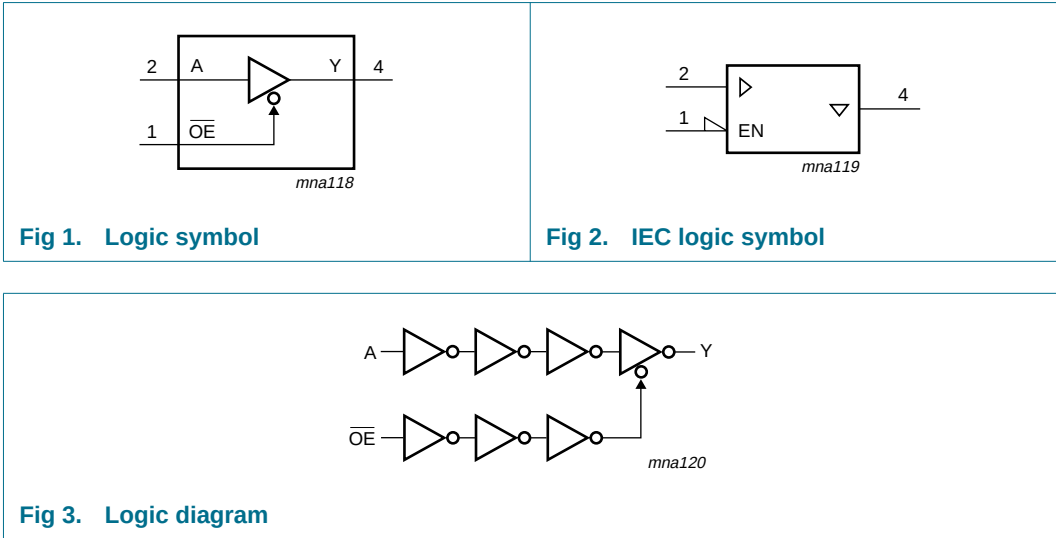
Type number	Package			
	Temperature range	Name	Description	Version
74HC1G125				
74HC1G125GW	-40°C to $+125^{\circ}\text{C}$	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74HC1G125GV	-40°C to $+125^{\circ}\text{C}$	SC-74A	plastic surface mounted package; 5 leads	SOT753
74HCT1G125				
74HCT1G125GW	-40°C to $+125^{\circ}\text{C}$	TSSOP5	plastic thin shrink small outline package; 5 leads; body width 1.25 mm	SOT353-1
74HCT1G125GV	-40°C to $+125^{\circ}\text{C}$	SC-74A	plastic surface mounted package; 5 leads	SOT753

5. Marking

Table 3: Marking

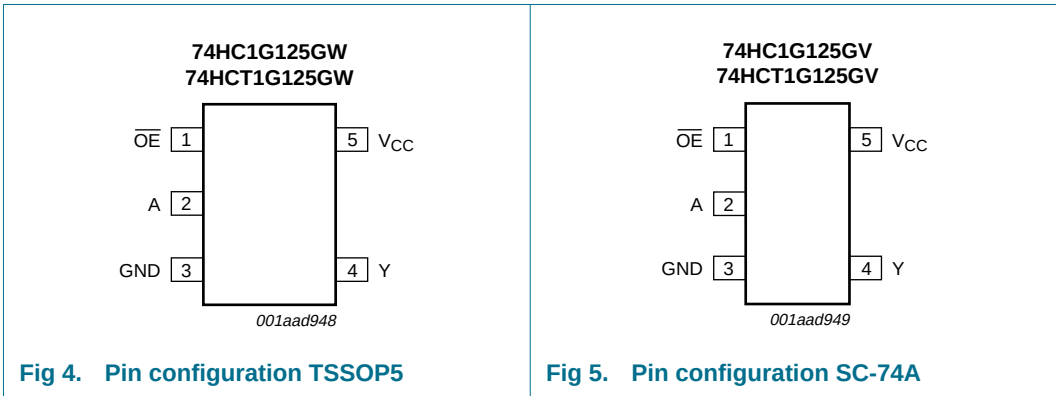
Type number	Marking code
74HC1G125GW	HM
74HC1G125GV	H25
74HCT1G125GW	TM
74HCT1G125GV	T25

6. Functional diagram



7. Pinning information

7.1 Pinning



7.2 Pin description

Table 4: Pin description

Symbol	Pin	Description
$\overline{\text{OE}}$	1	output enable input (active LOW)
A	2	data input
GND	3	ground (0 V)
Y	4	data output
V _{CC}	5	supply voltage

8. Functional description

8.1 Function table

Table 5: Function table ^[1]

Control	Input	Output
OE	A	Y
L	L	L
L	H	H
H	X	Z

- [1] H = HIGH voltage level;
 L = LOW voltage level;
 X = don't care;
 Z = high-impedance OFF-state.

9. Limiting values

Table 6: Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CC}	supply voltage		-0.5	+7.0	V
I_{IK}	input clamping current	$V_I < -0.5\text{ V}$ or $V_I > V_{CC} + 0.5\text{ V}$	^[1] -	±20	mA
I_{OK}	output clamping current	$V_O < -0.5\text{ V}$ or $V_O > V_{CC} + 0.5\text{ V}$	^[1] -	±20	mA
I_O	output current	$V_O = -0.5\text{ V}$ to $(V_{CC} + 0.5\text{ V})$	^[1] -	±35	mA
I_{CC}	quiescent supply current		-	70	mA
I_{GND}	ground current		-	-70	mA
T_{stg}	storage temperature		-65	+150	°C
P_{tot}	total power dissipation	$T_{amb} = -40\text{ °C}$ to $+125\text{ °C}$	^[2] -	200	mW

- [1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.
 [2] Above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.

10. Recommended operating conditions

Table 7: Recommended operating conditions

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
74HC1G125						
V_{CC}	supply voltage		2.0	5.0	6.0	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 2.0\text{ V}$	-	-	1000	ns
		$V_{CC} = 4.5\text{ V}$	-	-	500	ns
		$V_{CC} = 6.0\text{ V}$	-	-	400	ns
74HCT1G125						
V_{CC}	supply voltage		4.5	5.0	5.5	V
V_I	input voltage		0	-	V_{CC}	V
V_O	output voltage		0	-	V_{CC}	V
T_{amb}	ambient temperature		-40	+25	+125	°C
t_r, t_f	input rise and fall times	$V_{CC} = 4.5\text{ V}$	-	-	500	ns

11. Static characteristics

Table 8: Static characteristics 74HC1G125

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40\text{ °C to }+85\text{ °C}$ [1]						
V_{IH}	HIGH-state input voltage	$V_{CC} = 2.0\text{ V}$	1.5	1.2	-	V
		$V_{CC} = 4.5\text{ V}$	3.15	2.4	-	V
		$V_{CC} = 6.0\text{ V}$	4.2	3.2	-	V
V_{IL}	LOW-state input voltage	$V_{CC} = 2.0\text{ V}$	-	0.8	0.5	V
		$V_{CC} = 4.5\text{ V}$	-	2.1	1.35	V
		$V_{CC} = 6.0\text{ V}$	-	2.8	1.8	V
V_{OH}	HIGH-state output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20\text{ }\mu\text{A}; V_{CC} = 2.0\text{ V}$	1.9	2.0	-	V
		$I_O = -20\text{ }\mu\text{A}; V_{CC} = 4.5\text{ V}$	4.4	4.5	-	V
		$I_O = -20\text{ }\mu\text{A}; V_{CC} = 6.0\text{ V}$	5.9	6.0	-	V
		$I_O = -6.0\text{ mA}; V_{CC} = 4.5\text{ V}$	3.84	4.32	-	V
		$I_O = -7.8\text{ mA}; V_{CC} = 6.0\text{ V}$	5.34	5.81	-	V
V_{OL}	LOW-state output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20\text{ }\mu\text{A}; V_{CC} = 2.0\text{ V}$	-	0	0.1	V
		$I_O = 20\text{ }\mu\text{A}; V_{CC} = 4.5\text{ V}$	-	0	0.1	V
		$I_O = 20\text{ }\mu\text{A}; V_{CC} = 6.0\text{ V}$	-	0	0.1	V
		$I_O = 6.0\text{ mA}; V_{CC} = 4.5\text{ V}$	-	0.15	0.33	V
		$I_O = 7.8\text{ mA}; V_{CC} = 6.0\text{ V}$	-	0.16	0.33	V

Table 8: Static characteristics 74HC1G125 ...continued

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I_{LI}	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	1.0	μ A
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	5	μ A
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	10	μ A
C_i	input capacitance		-	1.5	-	pF
$T_{amb} = -40$ °C to $+125$ °C						
V_{IH}	HIGH-state input voltage	$V_{CC} = 2.0$ V	1.5	-	-	V
		$V_{CC} = 4.5$ V	3.15	-	-	V
		$V_{CC} = 6.0$ V	4.2	-	-	V
V_{IL}	LOW-state input voltage	$V_{CC} = 2.0$ V	-	-	0.5	V
		$V_{CC} = 4.5$ V	-	-	1.35	V
		$V_{CC} = 6.0$ V	-	-	1.8	V
V_{OH}	HIGH-state output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = -20$ μ A; $V_{CC} = 2.0$ V	1.9	-	-	V
		$I_O = -20$ μ A; $V_{CC} = 4.5$ V	4.4	-	-	V
		$I_O = -20$ μ A; $V_{CC} = 6.0$ V	5.9	-	-	V
		$I_O = -6.0$ mA; $V_{CC} = 4.5$ V	3.7	-	-	V
		$I_O = -7.8$ mA; $V_{CC} = 6.0$ V	5.2	-	-	V
V_{OL}	LOW-state output voltage	$V_I = V_{IH}$ or V_{IL}				
		$I_O = 20$ μ A; $V_{CC} = 2.0$ V	-	-	0.1	V
		$I_O = 20$ μ A; $V_{CC} = 4.5$ V	-	-	0.1	V
		$I_O = 20$ μ A; $V_{CC} = 6.0$ V	-	-	0.1	V
		$I_O = 6.0$ mA; $V_{CC} = 4.5$ V	-	-	0.4	V
		$I_O = 7.8$ mA; $V_{CC} = 6.0$ V	-	-	0.4	V
I_{LI}	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	1.0	μ A
I_{OZ}	OFF-state output current	$V_I = V_{IH}$ or V_{IL} ; $V_O = V_{CC}$ or GND; $V_{CC} = 6.0$ V	-	-	10	μ A
I_{CC}	quiescent supply current	$V_I = V_{CC}$ or GND; $I_O = 0$ A; $V_{CC} = 6.0$ V	-	-	20	μ A

[1] All typical values are measured at $T_{amb} = 25$ °C.

Table 9: Static characteristics 74HCT1G125

At recommended operating conditions; voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
T_{amb} = -40 °C to +85 °C [1]						
V _{IH}	HIGH-state input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	V
V _{IL}	LOW-state input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	V
V _{OH}	HIGH-state output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = -20 µA	4.4	4.5	-	V
		I _O = -6.0 mA	3.84	4.32	-	V
V _{OL}	LOW-state output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 µA	-	0	0.1	V
		I _O = 6.0 mA	-	0.16	0.33	V
I _{LI}	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	1.0	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	-	5	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	10	µA
ΔI _{CC}	additional quiescent supply current	V _I = V _{CC} - 2.1 V; I _O = 0 A; V _{CC} = 4.5 V to 5.5 V	-	-	500	µA
C _i	input capacitance		-	1.5	-	pF
T_{amb} = -40 °C to +125 °C						
V _{IH}	HIGH-state input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	-	-	V
V _{IL}	LOW-state input voltage	V _{CC} = 4.5 V to 5.5 V	-	-	0.8	V
V _{OH}	HIGH-state output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = -20 µA	4.4	-	-	V
		I _O = -6.0 mA	3.7	-	-	V
V _{OL}	LOW-state output voltage	V _I = V _{IH} or V _{IL} ; V _{CC} = 4.5 V				
		I _O = 20 µA	-	-	0.1	V
		I _O = 6.0 mA	-	-	0.4	V
I _{LI}	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	1.0	µA
I _{OZ}	OFF-state output current	V _I = V _{IH} or V _{IL} ; V _O = V _{CC} or GND; V _{CC} = 5.5 V	-	-	10	µA
I _{CC}	quiescent supply current	V _I = V _{CC} or GND; I _O = 0 A; V _{CC} = 6.0 V	-	-	20	µA
ΔI _{CC}	additional quiescent supply current	V _I = V _{CC} - 2.1 V; I _O = 0 A; V _{CC} = 4.5 V to 5.5 V	-	-	850	µA

[1] All typical values are measured at T_{amb} = 25 °C.

12. Dynamic characteristics

Table 10: Dynamic characteristics 74HC1G125

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 8](#)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40\text{ °C to }+85\text{ °C}$ [1]						
t_{PHL} , t_{PLH}	propagation delay A to Y	see Figure 6				
		$V_{CC} = 2.0\text{ V}$	-	24	125	ns
		$V_{CC} = 4.5\text{ V}$	-	10	25	ns
		$V_{CC} = 5\text{ V}$; $C_L = 15\text{ pF}$	-	9	-	ns
		$V_{CC} = 6.0\text{ V}$	-	8	21	ns
t_{PZH} , t_{PZL}	3-state output enable time OE to Y	see Figure 7				
		$V_{CC} = 2.0\text{ V}$	-	19	155	ns
		$V_{CC} = 4.5\text{ V}$	-	9	31	ns
		$V_{CC} = 6.0\text{ V}$	-	7	26	ns
t_{PHZ} , t_{PLZ}	3-state output disable time OE to Y	see Figure 7				
		$V_{CC} = 2.0\text{ V}$	-	18	155	ns
		$V_{CC} = 4.5\text{ V}$	-	12	31	ns
		$V_{CC} = 6.0\text{ V}$	-	11	26	ns
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC}$	[2]	-	30	pF
$T_{amb} = -40\text{ °C to }+125\text{ °C}$						
t_{PHL} , t_{PLH}	propagation delay A to Y	see Figure 6				
		$V_{CC} = 2.0\text{ V}$	-	-	150	ns
		$V_{CC} = 4.5\text{ V}$	-	-	30	ns
		$V_{CC} = 6.0\text{ V}$	-	-	26	ns
t_{PZH} , t_{PZL}	3-state output enable time OE to Y	see Figure 7				
		$V_{CC} = 2.0\text{ V}$	-	-	190	ns
		$V_{CC} = 4.5\text{ V}$	-	-	38	ns
		$V_{CC} = 6.0\text{ V}$	-	-	32	ns
t_{PHZ} , t_{PLZ}	3-state output disable time OE to Y	see Figure 7				
		$V_{CC} = 2.0\text{ V}$	-	-	190	ns
		$V_{CC} = 4.5\text{ V}$	-	-	38	ns
		$V_{CC} = 6.0\text{ V}$	-	-	32	ns

[1] All typical values are measured at $T_{amb} = 25\text{ °C}$.

[2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

Table 11: Dynamic characteristics 74HCT1G125

Voltages are referenced to GND (ground = 0 V); $C_L = 50$ pF unless otherwise specified; for test circuit see [Figure 8](#)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$T_{amb} = -40\text{ }^{\circ}\text{C to }+85\text{ }^{\circ}\text{C}$ [1]						
t_{PHL} , t_{PLH}	propagation delay A to Y	see Figure 6				
		$V_{CC} = 4.5\text{ V}$	-	11	30	ns
		$V_{CC} = 5\text{ V}; C_L = 15\text{ pF}$	-	10	-	ns
t_{PZH} , t_{PZL}	3-state output enable time $\overline{OE}$ to Y	$V_{CC} = 4.5\text{ V}$; see Figure 7	-	10	35	ns
t_{PHZ} , t_{PLZ}	3-state output disable time $\overline{OE}$ to Y	$V_{CC} = 4.5\text{ V}$; see Figure 7	-	11	31	ns
C_{PD}	power dissipation capacitance	$V_I = \text{GND to } V_{CC} - 1.5\text{ V}$	[2] -	27	-	pF
$T_{amb} = -40\text{ }^{\circ}\text{C to }+125\text{ }^{\circ}\text{C}$						
t_{PHL} , t_{PLH}	propagation delay A to Y	$V_{CC} = 4.5\text{ V}$; see Figure 6	-	-	36	ns
t_{PZH} , t_{PZL}	3-state output enable time $\overline{OE}$ to Y	$V_{CC} = 4.5\text{ V}$; see Figure 7	-	-	42	ns
t_{PHZ} , t_{PLZ}	3-state output disable time $\overline{OE}$ to Y	$V_{CC} = 4.5\text{ V}$; see Figure 7	-	-	38	ns

[1] All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

[2] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of the outputs.

13. Waveforms

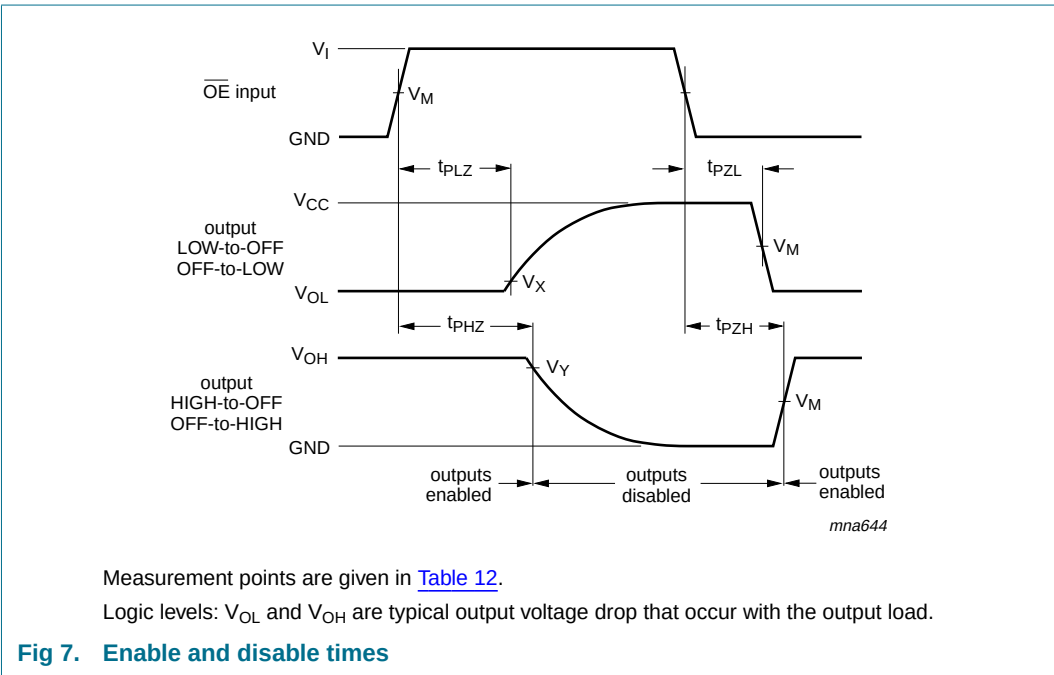
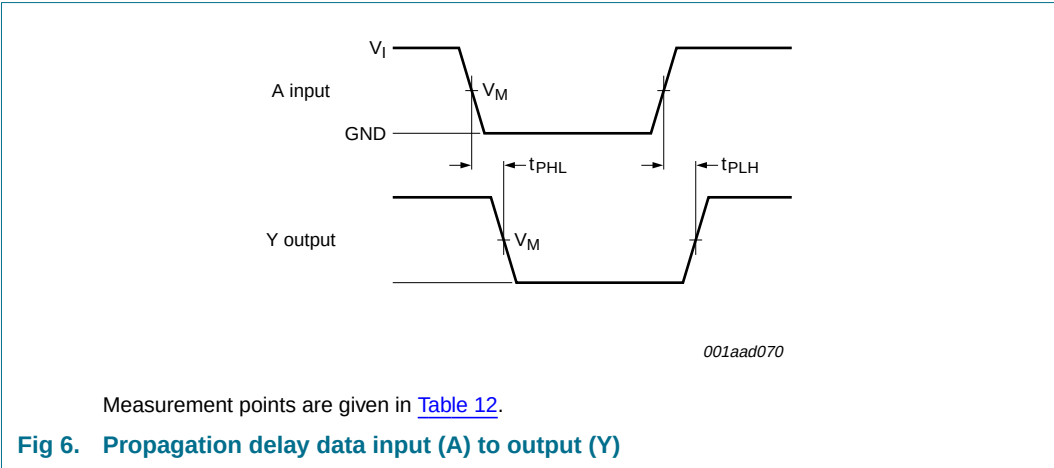


Table 12: Measurement points

Type	Input	Output		
	V_M	V_M	V_X	V_Y
74HC1G125	$0.5V_{CC}$	$0.5V_{CC}$	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$
74HCT1G125	1.3 V	1.3 V	$V_{OL} + 0.3\text{ V}$	$V_{OH} - 0.3\text{ V}$

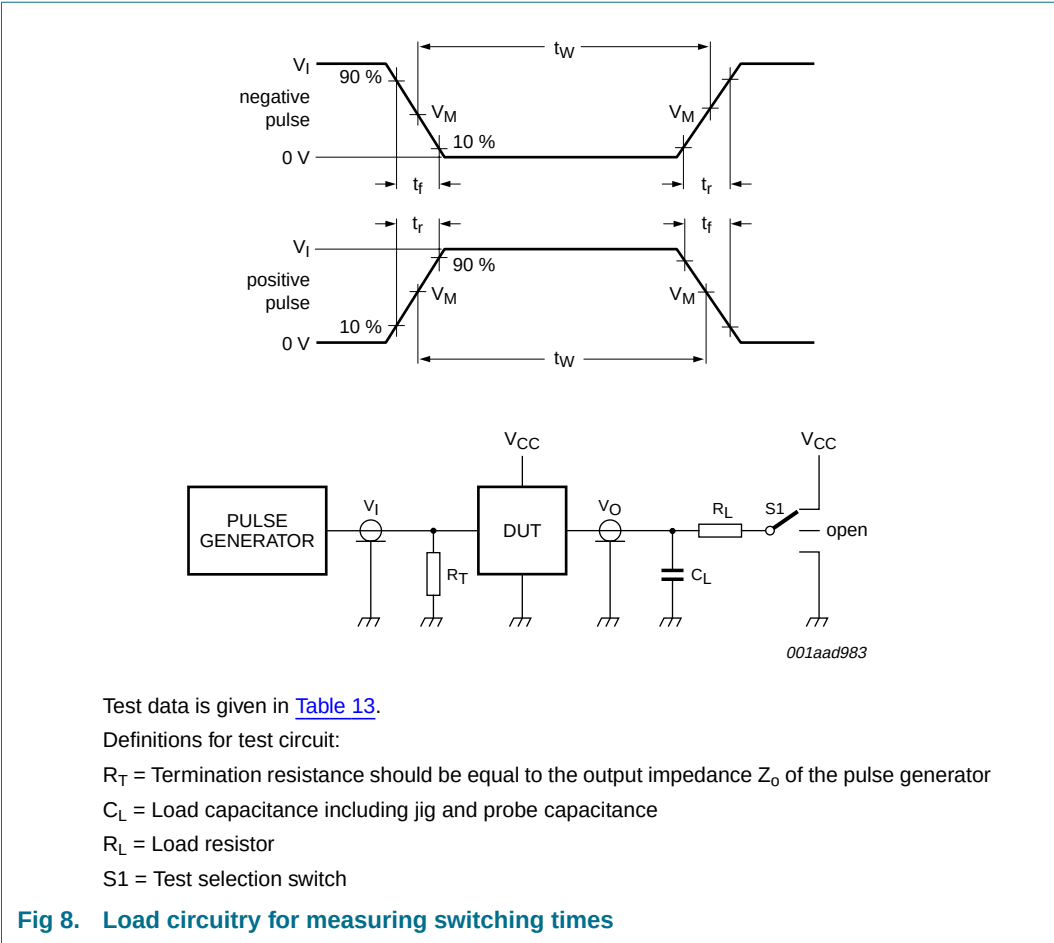


Table 13: Test data

Type	Input		Load		S1 position		
	V_I	t_r, t_f	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
74HC1G125	V_{CC}	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}
74HCT1G125	3 V	6 ns	15 pF, 50 pF	1 k Ω	open	GND	V_{CC}

14. Package outline

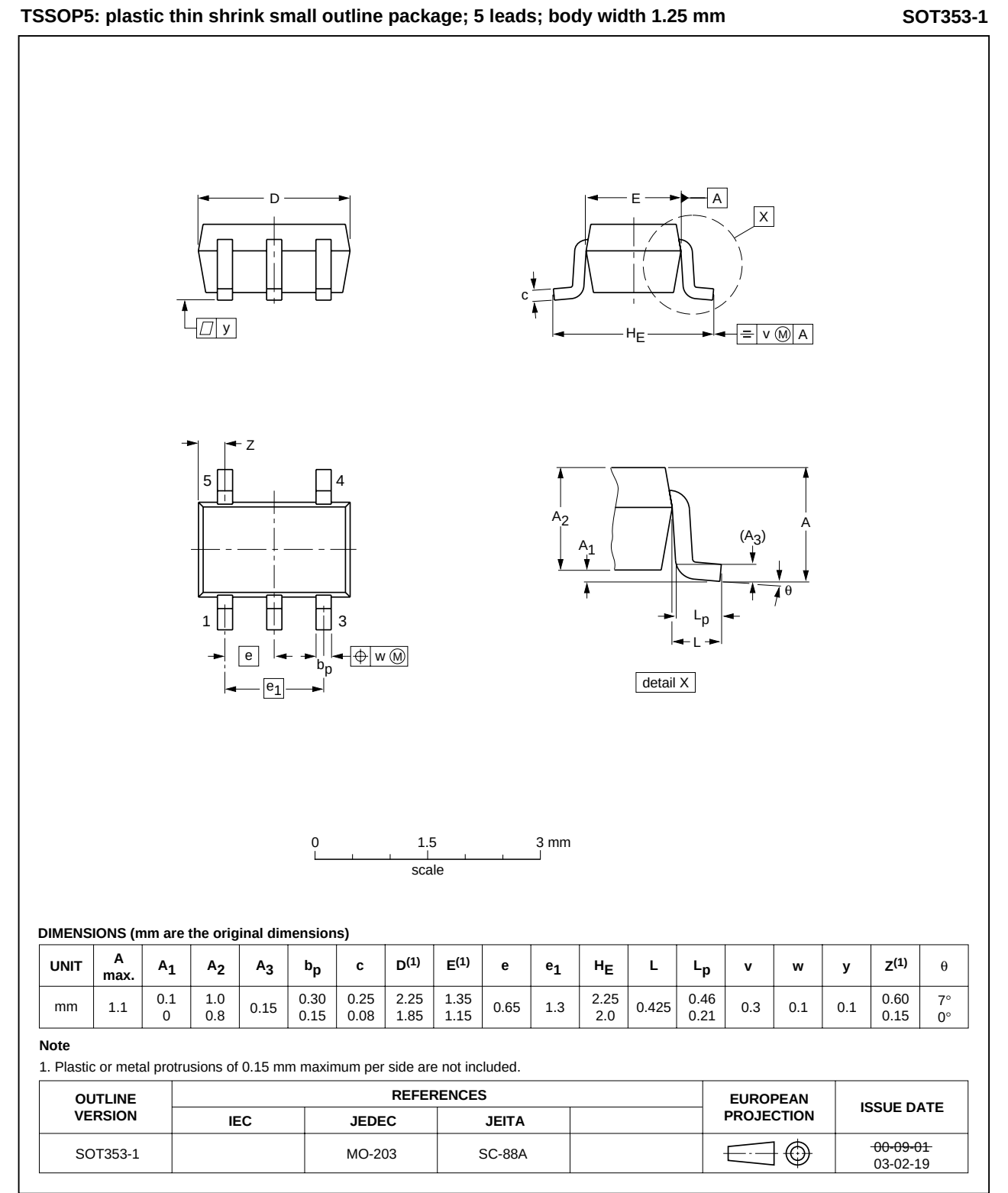


Fig 9. Package outline SOT353-1 (TSSOP5)

Plastic surface mounted package; 5 leads

SOT753

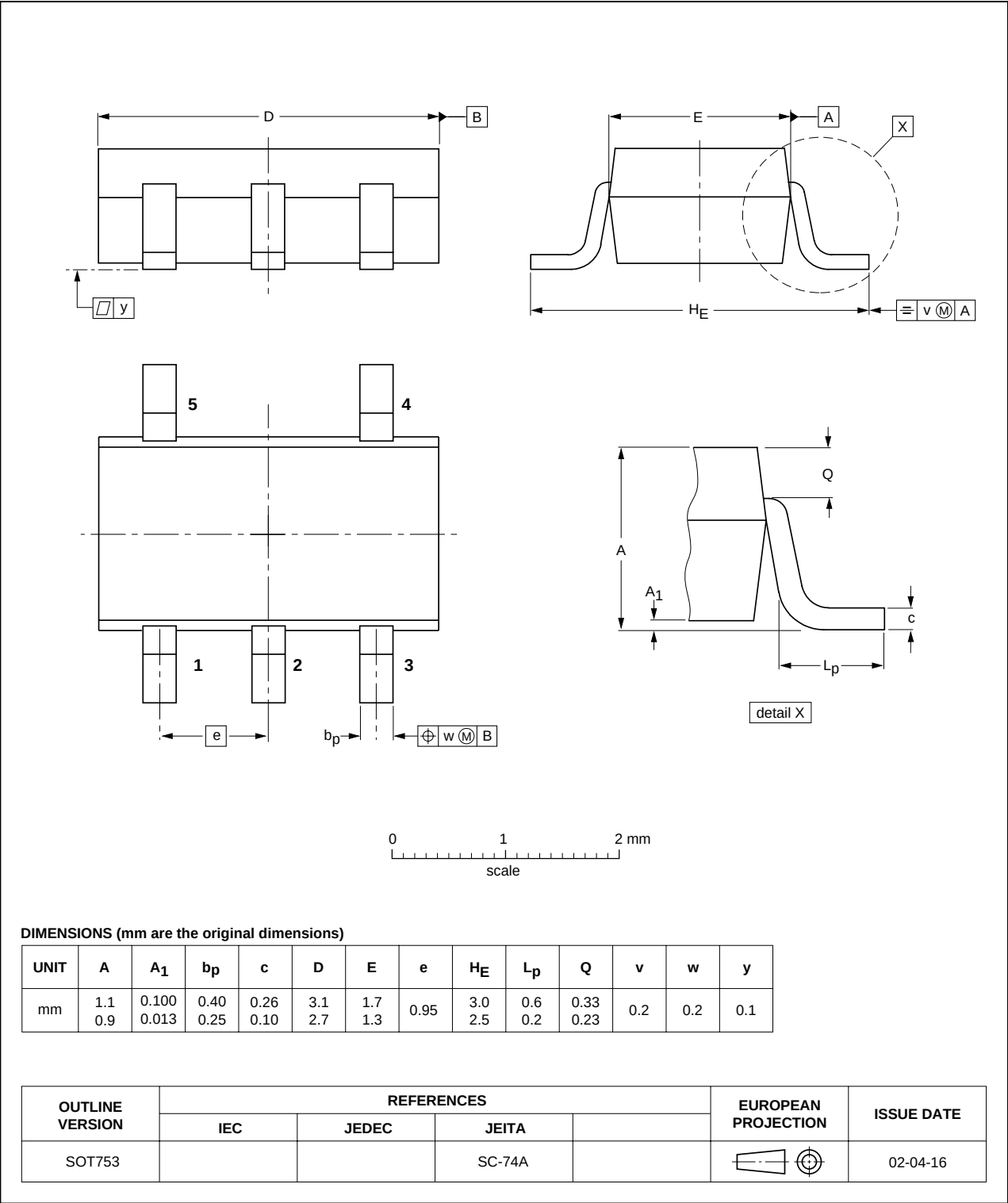


Fig 10. Package outline SOT753 (SC-74A)

15. Abbreviations

Table 14: Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
ESD	ElectroStatic Discharge
HBM	Human Body Model
TTL	Transistor-Transistor Logic
MM	Machine Model

16. Revision history

Table 15: Revision history

Document ID	Release date	Data sheet status	Change notice	Doc. number	Supersedes
74HC_HCT1G125_5	20051223	Product data sheet	ECN05_085	-	74HC_HCT1G125_4
Modifications: - The format of this data sheet has been redesigned to comply with the new presentation and information standard of Philips Semiconductors. - In Table 6 "Limiting values" I_O: changed max value ± 12.5 into ± 35 I_{CC}: changed max value 25 into 70 I_{GND}: changed max value -25 into -70 - In Table 8 "Static characteristics 74HC1G125"; $T_{amb} = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ V_{OH}: changed condition $I_O = -2.0\text{ mA}$ into $I_O = -6.0\text{ mA}$ and min value from 4.13 into 3.84 V_{OH}: changed condition $I_O = -2.6\text{ mA}$ into $I_O = -7.8\text{ mA}$ and min value from 5.63 into 5.34 V_{OL}: changed condition $I_O = 2.0\text{ mA}$ into $I_O = 6.0\text{ mA}$ V_{OL}: changed condition $I_O = 2.6\text{ mA}$ into $I_O = 7.8\text{ mA}$ - In Table 8 "Static characteristics 74HC1G125"; $T_{amb} = -40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ V_{OH}: changed condition $I_O = -2.0\text{ mA}$ into $I_O = -6.0\text{ mA}$ V_{OL}: changed condition $I_O = 2.0\text{ mA}$ into $I_O = 6.0\text{ mA}$ - In Table 9 "Static characteristics 74HCT1G125"; $T_{amb} = -40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ V_{OH}: changed condition $I_O = -2.0\text{ mA}$ into $I_O = -6.0\text{ mA}$ and min value from 4.13 into 3.84 V_{OL}: changed condition $I_O = 2.0\text{ mA}$ into $I_O = 6.0\text{ mA}$ and typ value from 0.15 into 0.16 - In Table 9 "Static characteristics 74HCT1G125"; $T_{amb} = -40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$ V_{OH}: changed condition $I_O = -2.0\text{ mA}$ into $I_O = -6.0\text{ mA}$ V_{OL}: changed condition $I_O = 2.0\text{ mA}$ into $I_O = 6.0\text{ mA}$					
74HC_HCT1G125_4	20040727	Product specification	-	9397 750 13725	74HC_HCT1G125_3
74HC_HCT1G125_3	20020517	Product specification	-	9397 750 09718	74HC_HCT1G125_2
74HC_HCT1G125_2	20010302	Product specification	-	9397 750 07966	74HC_HCT1G125_1
74HC_HCT1G125_1	19981110	Product specification	-	9397 750 03693	-

17. Data sheet status

Level	Data sheet status ^[1]	Product status ^{[2] [3]}	Definition
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[3] For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

18. Definitions

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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21. Contact information

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For sales office addresses, send an email to: sales.addresses@www.semiconductors.philips.com

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Date of release: 23 December 2005
Document number: 74HC_HCT1G125_5

Published in The Netherlands